## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet



#### FMMT591 TRANSISTOR (PNP)



**SOT - 23** 



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

#### **FEATURES**

Low equivalent on-resistance

Marking:591

#### MAXIMUM RATINGS (T<sub>a</sub>=25℃ unless otherwise noted)

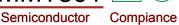
Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-80	٧
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	٧
Ic	Collector Current	-1	Α
I <sub>CM</sub>	Peak Pulse Current	-2	Α
Pc	Collector Power Dissipation	250	mW
R <sub>OJA</sub>	Thermal Resistance From Junction To Ambient	500	°C/W
Tj	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~+150	$^{\circ}$

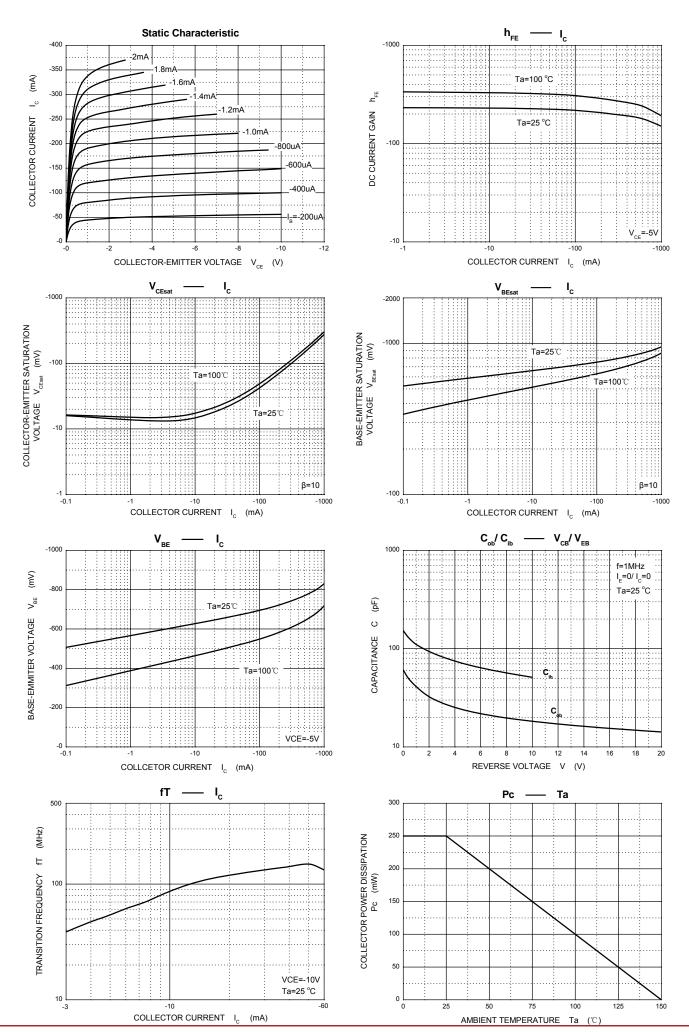
#### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-80			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> <sup>1</sup>	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-60			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-60V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0			-0.1	μΑ
	h <sub>FE(1)</sub>	$V_{CE}$ =-5 $V$ , $I_{C}$ =-1 $mA$	100			
DC assument weigh	h <sub>FE(2)</sub> <sup>1</sup>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-500mA	100		300	
DC current gain	h <sub>FE(3)</sub> 1	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A	80			
	h <sub>FE(4)</sub> 1	V <sub>CE</sub> =-5V, I <sub>C</sub> =-2A	15			
Callactor emitter acturation valtage	V <sub>CE(sat)1</sub> 1	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA			-0.3	V
Collector-emitter saturation voltage	V <sub>CE(sat)2</sub> 1	I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA			-0.6	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub> <sup>1</sup>	I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA			-1.2	V
Base-emitter voltage	V <sub>BE</sub> <sup>1</sup>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A			-1	V
Transition frequency	f⊤	V <sub>CE</sub> =-10V,I <sub>C</sub> =-50mA,,f=100MHz	150			MHz
Collector output capacitance	Cob	V <sub>CB</sub> =-10V,f=1MHz			10	pF

<sup>&</sup>lt;sup>1</sup>Measured under pulsed conditions, Pulse width=300µs, Duty cycle≤2%.

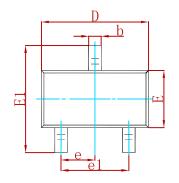


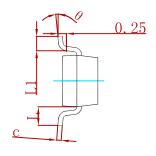


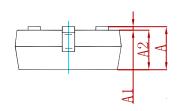




#### **PACKAGE MECHANICAL DATA**

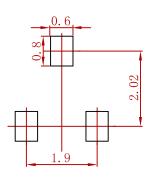






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Зупьоі	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
FMMT591	SOT-23	3000



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